Triacs BT139B series

#### **GENERAL DESCRIPTION**

#### **QUICK REFERENCE DATA**

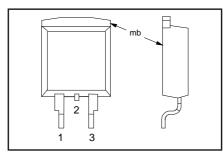
Passivated triacs in a plastic envelope suitable for surface mounting, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

SYMBOL	PARAMETER	MAX.	MAX.	UNIT
	BT139B- BT139B- BT139B-	600 600F 600G	800 800F 800G	
$V_{DRM}$	Repetitive peak off-state	600	800	V
I <sub>T(RMS)</sub> I <sub>TSM</sub>	voltages RMS on-state current Non-repetitive peak on-state current	16 140	16 140	A A

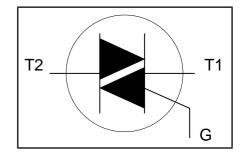
#### **PINNING - SOT404**

PIN	DESCRIPTION			
1	main terminal 1			
2	main terminal 2			
3	gate			
mb	main terminal 2			

### **PIN CONFIGURATION**



### **SYMBOL**



### **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MA	۸X.	UNIT
V <sub>DRM</sub>	Repetitive peak off-state voltages		-	<b>-600</b> 600 <sup>1</sup>	<b>-800</b> 800	V
I <sub>T(RMS)</sub>	RMS on-state current Non-repetitive peak on-state current	full sine wave; $T_{mb} \le 99 ^{\circ}C$ full sine wave; $T_{j} = 25 ^{\circ}C$ prior to surge	-		6	А
		t = 20 ms	-		10	A
l <sup>2</sup> t	12t for fusing	t = 16.7 ms	-		50	A A <sup>2</sup> s
dl <sub>⊤</sub> /dt	l <sup>2</sup> t for fusing Repetitive rate of rise of on-state current after	I = 10  ms $I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A};$ $I_{G} = 0.2 \text{ A}$	-	9	0	AS
	triggering	T2+ G+	-	5	0	A/μs
		T2+ G-	-		0	A/μs
		T2- G-	-		0	A/μs
١.	Deals and assument	T2- G+	-		0	A/μs
I I <sub>GM</sub>	Peak gate current		-	4	<u> </u>	l A V
$\begin{array}{ c c }\hline V_{GM} \\ P_{GM} \end{array}$	Peak gate voltage Peak gate power		]	ì	<u>2</u> 5	l w l
P <sub>G(AV)</sub>	Average gate power	over any 20 ms period	_		.5	W
T <sub>sta</sub>	Storage temperature	are, any 20 me period	-40		50	l °C
T <sub>stg</sub>	Operating junction temperature		-		25	°C

<sup>1</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/ $\mu$ s.

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# THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th j-mb</sub>	Thermal resistance junction to mounting base Thermal resistance junction to ambient	full cycle half cycle minimum footprint, FR4 board		- - 55	1.2 1.7 -	K/W K/W K/W

# STATIC CHARACTERISTICS

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.		MAX.		UNIT
_		BT139B-				F	G	
I <sub>GT</sub>	Gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}$		_	0.5		<b>5</b> 0	
		T2+ G+	-	5	35	25	50	m A
		T2+ G-	-	8	35	25	50	mA.
		T2- G-	-	10	35	25	50	mA
		T2- G+	-	22	70	70	100	mA
I <sub>L</sub>	Latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$						
_		T2+ G+	-	7	40	40	60	mA
		T2+ G-	-	20	60	60	90	mA
		T2- G-	-	8	40	40	60	mA
		T2- G+	-	10	60	60	90	mA
I <sub>H</sub>	Holding current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}$	-	6	30	30	60	mA
$V_T$	On-state voltage	$I_{T} = 20 \text{ A}$	_	1.2		1.6		V
$V_{GT}^{'}$	Gate trigger voltage	$\dot{V}_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}$	-	0.7		1.5		V
Gi		$V_D^D = 400 \text{ V}; I_T = 0.1 \text{ A};$	0.25	0.4		-		V
		T <sub>i</sub> = 125 °C						
I <sub>D</sub>	Off-state leakage current	$V_D = V_{DRM(max)};$ $T_i = 125 ^{\circ}C$	-	0.1		0.5		mA

# **DYNAMIC CHARACTERISTICS**

T<sub>i</sub> = 25 °C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS		MIN.		TYP.	MAX.	UNIT
dV <sub>D</sub> /dt	Critical rate of rise of off-state voltage	BT139B- $V_{DM} = 67\% V_{DRM(max)};$ $T_j = 125 °C;$ exponential	 100	<b>F</b> 50	<b>G</b> 200	250	-	V/μs
dV <sub>com</sub> /dt	Critical rate of change of commutating voltage	waveform; gate open circuit $V_{DM} = 400 \text{ V}; T_j = 95 ^{\circ}\text{C};$ $I_{T(RMS)} = 16 \text{ A};$ $dI_{com}/dt = 7.2 \text{ A/ms}; gate$	-	-	10	20	-	V/μs
$\mathbf{t}_{gt}$	Gate controlled turn-on time	open circuit $I_{TM} = 20 \text{ A}$ ; $V_D = V_{DRM(max)}$ ; $I_G = 0.1 \text{ A}$ ; $dI_G/dt = 5 \text{ A}/\mu \text{s}$	-	-	-	2	-	μs

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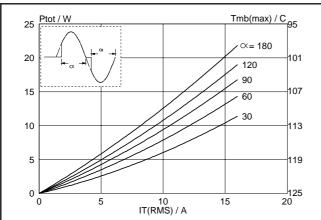


Fig.1. Maximum on-state dissipation,  $P_{tot}$ , versus rms on-state current,  $I_{T(RMS)}$ , where  $\alpha =$  conduction angle.

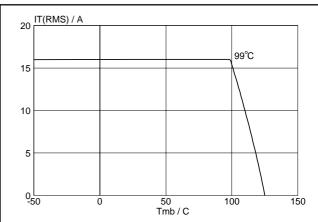


Fig.4. Maximum permissible rms current  $I_{T(RMS)}$ , versus mounting base temperature  $T_{mb}$ .

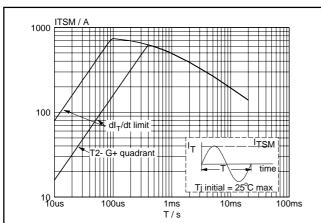


Fig.2. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus pulse width  $t_p$ , for sinusoidal currents,  $t_p \le 20$ ms.

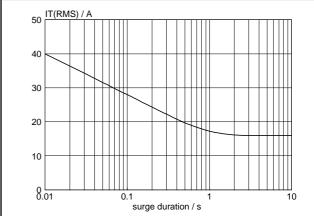


Fig.5. Maximum permissible repetitive rms on-state current  $I_{T(RMS)}$ , versus surge duration, for sinusoidal currents, f = 50 Hz;  $T_{mb} \le 99$  °C.

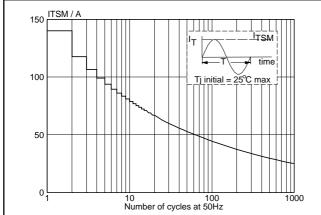


Fig.3. Maximum permissible non-repetitive peak on-state current  $I_{TSM}$ , versus number of cycles, for sinusoidal currents, f = 50 Hz.

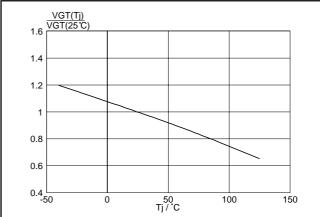
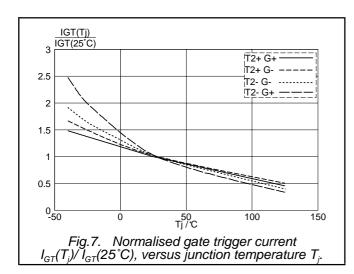


Fig.6. Normalised gate trigger voltage  $V_{GT}(T_i)/V_{GT}(25^{\circ}C)$ , versus junction temperature  $T_i$ .

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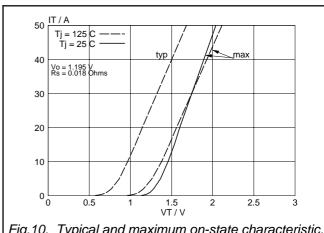
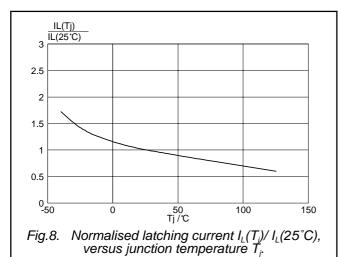


Fig. 10. Typical and maximum on-state characteristic.



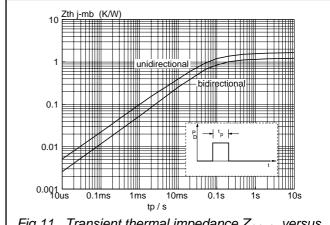


Fig.11. Transient thermal impedance  $Z_{th j-mb}$ , versus pulse width  $t_{\rm p}$ 

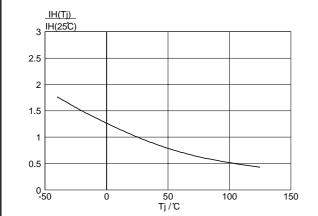


Fig.9. Normalised holding current  $I_H(T_i)/I_H(25^{\circ}\text{C})$ , versus junction temperature  $T_j$ .

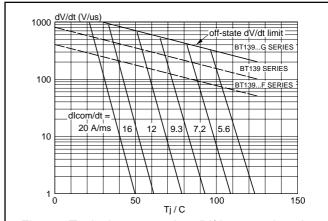
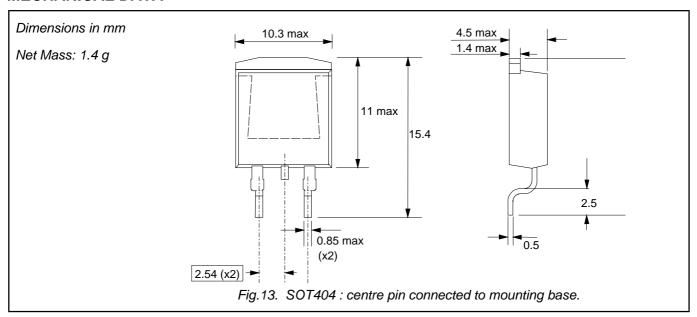


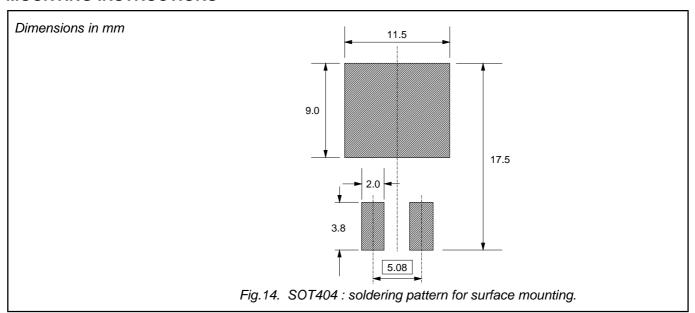
Fig.12. Typical commutation dV/dt versus junction temperature, parameter commutation dl<sub>T</sub>/dt. The triac should commutate when the dV/dt is below the value on the appropriate curve for pre-commutation  $dI_{\tau}/dt$ .

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### **MECHANICAL DATA**



# **MOUNTING INSTRUCTIONS**



### **Notes**

1. Plastic meets UL94 V0 at 1/8".

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#### **DEFINITIONS**

DATA SHEET STATUS						
DATA SHEET STATUS <sup>2</sup>	PRODUCT STATUS <sup>3</sup>	DEFINITIONS				
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice				
Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in ordere to improve the design and supply the best possible product				
Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A				

#### Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### Application information

Where application information is given, it is advisory and does not form part of the specification.

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